

## Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Diodes Incorporated](#)  
[FMMV105GTA](#)

For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)

# SOT23 SILICON PLANAR VARIABLE CAPACITANCE DIODE

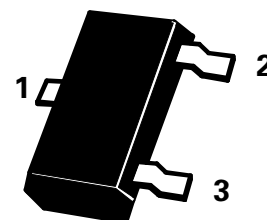
## FMMV105G

ISSUE 4 – JANUARY 1998

### PIN CONFIGURATION



PARTMARKING DETAILS  
 FMMV105G – 4EZ



SOT23

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	$V_{BR}$	30			V	$I_R = 10\mu A$
Reverse current	$I_R$			10	nA	$V_R = 28V$
Series Inductance	$L_S$		3.0		nH	$f=250MHz$
Diode Capacitance Temperature Coefficient	$T_{CC}$		280		ppm/ $^{\circ}C$	$V_R = 3V, f=1MHz$

### TUNING CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Diode Capacitance	$C_d$	1.8		2.8	pF	$V_R = 25V, f=1MHz$
Capacitance Ratio	$C_d / C_d$	4.0		6.0		$V_R = 3V/25V, f=1MHz$
Figure of MERIT	Q	250	350			$V_R = 3V, f=50MHz$

Spice parameter data is available upon request for this device